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(54) Title: TWO STEP POLY ETCH LDMOS GATE FORMATION

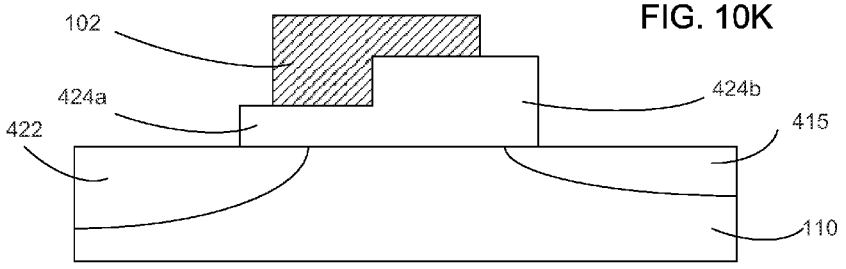


FIG. 10K

(57) Abstract: A method of making a transistor includes etching a first side of a gate, the gate including an oxide layer formed over a substrate and a conductive material formed over the oxide layer, the etching removing a first portion of the conductive material, implanting an impurity region into the substrate such that the impurity region is self-aligned, and etching a second side of the gate to remove a second portion of the conductive material.

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